

Amendments to the Claims:

This listing of claims replaces all prior versions and listings of claims in the application:

Listing of Claims:

1-5. (Canceled)

6. (Currently amended) A method of manufacturing a light emitting device, said method comprising:

forming a first insulating film, wherein the first insulating film includes a first opening;
forming at least a transparent protrusion to overlap the first opening;
forming a [[pixel]] first electrode to overlap the transparent protrusion;
forming a light emitting layer to overlap the [[pixel]] first electrode; and
forming [[an]] a second electrode over the light emitting layer.

7-13. (Canceled)

14. (Currently amended) A method according to claim 6, further comprising:
forming [[an]] a second insulating film in a transverse direction of the transparent protrusion, wherein the second insulating film has a [[high]] light absorption property.

15. (Currently amended) A method according to claim 6, further comprising:
forming a thin film transistor [[an]] over a substrate, wherein the thin film transistor comprises a semiconductor film and a gate electrode;
forming an insulating film over the thin film transistor;
forming a [[first]] second opening in the first insulating film; and
forming a wiring over the first insulating film, wherein the wiring is electrically connected to the semiconductor film through the [[first]] second opening; and

forming at least one second opening in the insulating film.

16. (Currently amended) A method according to claim 6, further comprising:

forming a thin film transistor ~~[[øñ]]~~ over a substrate, wherein the thin film transistor comprises a semiconductor film and a gate electrode;

~~forming an insulating film over the thin film transistor, wherein the insulating film has a high light absorption property;~~

forming a ~~[[first]]~~ second opening in the first insulating film; and

forming a wiring over the first insulating film, wherein the wiring is electrically connected to the semiconductor film through the ~~[[first]]~~ second opening; ~~[[and]]~~

~~forming at least one second opening in the insulating film
wherein the first insulating film has a light absorption property.~~

17. (Currently amended) A method according to claim 6, further comprising:

forming a thin film transistor ~~[[øñ]]~~ over a substrate, wherein the thin film transistor comprises a semiconductor film and a gate electrode;

~~forming a first insulating film over the thin film transistor;~~

forming a ~~[[first]]~~ second opening in the first insulating film;

forming a wiring over the first insulating film, wherein the wiring is electrically connected to the semiconductor film through the ~~[[first]]~~ second opening;

forming a second insulating film in contact with the first insulating film; and

forming a ~~second~~ third opening in the second insulating film.

18. (Currently amended) A method according to claim 6, further comprising:

forming a thin film transistor ~~[[øñ]]~~ over a substrate, wherein the thin film transistor comprises a semiconductor film and a gate electrode;

~~forming a first insulating film over the thin film transistor;~~

forming a ~~[[first]]~~ second opening in the first insulating film;

forming a wiring over the first insulating film, wherein the wiring is electrically connected to the semiconductor film through the ~~[[first]]~~ second opening;

forming a second insulating film in contact with the first insulating film, wherein the second insulating film has a ~~[[high]]~~ light absorption property; and

forming a ~~second~~ third opening in the second insulating film.

19. (Previously Presented) A method according to claim 6, wherein the transparent protrusion comprises a microlens.

20. (Currently amended) A method according to claim 6, wherein the light emitting layer comprises ~~at least one of~~ an organic material ~~and an inorganic material~~.

21. (Currently amended) A method according to claim 6, wherein a surface of the second electrode in contact with the light emitting layer is uneven.

22-23. (Canceled)

24. (Currently amended) A method of manufacturing a light emitting device, said method comprising:

forming a first insulating film, wherein the first insulating film includes a first opening;

forming at least a protrusion having a property of transmitting light to overlap the first opening;

forming a ~~[[pixel]]~~ first electrode to overlap the protrusion;

forming a light emitting layer to overlap the ~~[[pixel]]~~ first electrode; and

forming ~~[[an]]~~ a second electrode over the light emitting layer.

25. (Currently amended) A method according to claim 24, further comprising:

forming ~~[[an]]~~ a second insulating film in a transverse direction of the protrusion, wherein the second insulating film has a ~~[[high]]~~ light absorption property.

26. (Currently amended) A method according to claim 24, further comprising:
forming a thin film transistor ~~[[an]]~~ over a substrate, wherein the thin film transistor comprises a semiconductor film and a gate electrode;

~~forming an insulating film over the thin film transistor;~~

forming a ~~[[first]]~~ second opening in the first insulating film; and

forming a wiring over the first insulating film, wherein the wiring is electrically connected to the semiconductor film through the ~~[[first]]~~ second opening; ~~and~~

~~forming at least one second opening in the insulating film.~~

27. (Currently amended) A method according to claim 24, further comprising:
forming a thin film transistor ~~[[an]]~~ over a substrate, wherein the thin film transistor comprises a semiconductor film and a gate electrode;

~~forming an insulating film over the thin film transistor, wherein the insulating film has a high light absorption property;~~

forming a ~~[[first]]~~ second opening in the first insulating film; and

forming a wiring over the first insulating film, wherein the wiring is electrically connected to the semiconductor film through the ~~[[first]]~~ second opening; and

~~forming at least one second opening in the insulating film~~

wherein the first insulating film has a light absorption property.

28. (Currently amended) A method according to claim 24, further comprising:
forming a thin film transistor ~~[[an]]~~ over a substrate, wherein the thin film transistor comprises a semiconductor film and a gate electrode;

~~forming a first insulating film over the thin film transistor;~~

forming a ~~[[first]]~~ second opening in the first insulating film;

forming a wiring over the first insulating film, wherein the wiring is electrically connected to the semiconductor film through the ~~[[first]]~~ second opening;
forming a second insulating film in contact with the first insulating film; and
forming a ~~second~~ third opening in the second insulating film.

29. (Currently amended) A method according to claim 24, further comprising:
forming a thin film transistor ~~[[on]]~~ over a substrate, wherein the thin film transistor comprises a semiconductor film and a gate electrode;
~~forming a first insulating film over the thin film transistor;~~
forming a ~~[[first]]~~ second opening in the first insulating film;
forming a wiring over the first insulating film, wherein the wiring is electrically connected to the semiconductor film through the ~~[[first]]~~ second opening;
forming a second insulating film in contact with the first insulating film, wherein the second insulating film has a ~~[[high]]~~ light absorption property; and
forming a ~~second~~ third opening in the second insulating film.

30. (Currently amended) A method according to claim 24, wherein the light emitting layer comprises ~~at least one of an organic material and an inorganic material.~~

31. (Currently amended) A method according to claim 24, wherein a surface of the second electrode in contact with the light emitting layer is uneven.

32. (Currently amended) A method of manufacturing a light emitting device, said method comprising:

forming a first insulating film, wherein the first insulating film includes a first opening;
forming at least a microlens to overlap the first opening;
forming a ~~[[pixel]]~~ first electrode to overlap the microlens;
forming a light emitting layer to overlap the ~~[[pixel]]~~ first electrode; and

forming ~~[[an]]~~ a second electrode over the light emitting layer.

33. (Currently amended) A method according to claim 32, further comprising:
forming ~~[[an]]~~ a second insulating film in a transverse direction of the microlens, wherein the second insulating film has a ~~[[high]]~~ light absorption property.

34. (Currently amended) A method according to claim 32, further comprising:
forming a thin film transistor ~~[[on]]~~ over a substrate, wherein the thin film transistor comprises a semiconductor film and a gate electrode;
~~forming an insulating film over the thin film transistor;~~
forming a ~~[[first]]~~ second opening in the first insulating film; and
forming a wiring over the first insulating film, wherein the wiring is electrically connected to the semiconductor film through the ~~[[first]]~~ second opening; ~~and~~
~~forming at least one second opening in the insulating film.~~

35. (Currently amended) A method according to claim 32, further comprising:
forming a thin film transistor ~~[[on]]~~ over a substrate, wherein the thin film transistor comprises a semiconductor film and a gate electrode;
~~forming an insulating film over the thin film transistor, wherein the insulating film has a high light absorption property;~~
forming a ~~[[first]]~~ second opening in the first insulating film; and
forming a wiring over the first insulating film, wherein the wiring is electrically connected to the semiconductor film through the ~~[[first]]~~ second opening; ~~and~~
~~forming at least one second opening in the insulating film~~
wherein the first insulating film has a light absorption property.

36. (Currently amended) A method according to claim 32, further comprising:

forming a thin film transistor ~~[[on]]~~ over a substrate, wherein the thin film transistor comprises a semiconductor film and a gate electrode;
~~forming a first insulating film over the thin film transistor;~~
forming a ~~[[first]]~~ second opening in the first insulating film;
forming a wiring over the first insulating film, wherein the wiring is electrically connected to the semiconductor film through the ~~[[first]]~~ second opening;
forming a second insulating film in contact with the first insulating film; and
forming a ~~second~~ third opening in the second insulating film.

37. (Currently amended) A method according to claim 32, further comprising:
forming a thin film transistor ~~[[on]]~~ over a substrate, wherein the thin film transistor comprises a semiconductor film and a gate electrode;
~~forming a first insulating film over the thin film transistor;~~
forming a ~~[[first]]~~ second opening in the first insulating film;
forming a wiring over the first insulating film, wherein the wiring is electrically connected to the semiconductor film through the ~~[[first]]~~ second opening;
forming a second insulating film in contact with the first insulating film, wherein the second insulating film has a ~~[[high]]~~ light absorption property; and
forming a ~~second~~ third opening in the second insulating film.

38. (Currently amended) A method according to claim 32, wherein the light emitting layer comprises ~~at least one of an organic material and an inorganic material.~~

39. (Currently amended) A method according to claim 32, wherein a surface of the second electrode in contact with the light emitting layer is uneven.

40. (Currently amended) A method of manufacturing a light emitting device, said method comprising:

forming a first insulating film, wherein the first insulating film includes a first opening;
forming at least a layer containing a transparent material to overlap the first opening;
forming a [[~~pixel~~]] first electrode to overlap the layer;
forming a light emitting layer to overlap the [[~~pixel~~]] first electrode; and
forming [[~~an~~]] a second electrode over the light emitting layer,
wherein a surface of the second electrode in contact with the light emitting layer is
uneven.

41. (Currently amended) A method according to claim 40, further comprising:
forming [[~~an~~]] a second insulating film in a transverse direction of the layer, wherein the
second insulating film has a [[~~high~~]] light absorption property.

42. (Currently amended) A method according to claim 40, further comprising:
forming a thin film transistor [[~~on~~]] over a substrate, wherein the thin film transistor
comprises a semiconductor film and a gate electrode;
forming an insulating film over the thin film transistor;
forming a [[~~first~~]] second opening in the first insulating film; and
forming a wiring over the first insulating film, wherein the wiring is electrically
connected to the semiconductor film through the [[~~first~~]] second opening; and
forming at least one second opening in the insulating film.

43. (Currently amended) A method according to claim 40, further comprising:
forming a thin film transistor [[~~on~~]] over a substrate, wherein the thin film transistor
comprises a semiconductor film and a gate electrode;
forming an insulating film over the thin film transistor, wherein the insulating film has a
high light absorption property;
forming a [[~~first~~]] second opening in the first insulating film; and

forming a wiring over the first insulating film, wherein the wiring is electrically connected to the semiconductor film through the ~~[[first]]~~ second opening; ~~and forming at least one second opening in the insulating film wherein the first insulating film has a light absorption property.~~

44. (Currently amended) A method according to claim 40, further comprising:
forming a thin film transistor ~~[[on]]~~ over a substrate, wherein the thin film transistor comprises a semiconductor film and a gate electrode;
~~forming a first insulating film over the thin film transistor;~~
forming a ~~[[first]]~~ second opening in the first insulating film;
forming a wiring over the first insulating film, wherein the wiring is electrically connected to the semiconductor film through the ~~[[first]]~~ second opening;
forming a second insulating film in contact with the first insulating film; and
forming a ~~second~~ third opening in the second insulating film.

45. (Currently amended) A method according to claim 40, further comprising:
forming a thin film transistor ~~[[on]]~~ over a substrate, wherein the thin film transistor comprises a semiconductor film and a gate electrode;
~~forming a first insulating film over the thin film transistor;~~
forming a ~~[[first]]~~ second opening in the first insulating film;
forming a wiring over the first insulating film, wherein the wiring is electrically connected to the semiconductor film through the ~~[[first]]~~ second opening;
forming a second insulating film in contact with the first insulating film, wherein the second insulating film has a ~~[[high]]~~ light absorption property; and
forming a ~~second~~ third opening in the second insulating film.

46. (Currently amended) A method according to claim 40, wherein the light emitting layer comprises ~~at least one of~~ an organic material ~~and an inorganic material.~~

47. (Previously Presented) A method according to claim 40, wherein the layer has a protrusion.

48. (Currently amended) A method of manufacturing a light emitting device, said method comprising:

forming a first insulating film, wherein the first insulating film includes a first opening;
forming at least a layer having a property of transmitting light to overlap the first opening;

forming a ~~[[pixel]]~~ first electrode to overlap the layer;
forming a light emitting layer to overlap the ~~[[pixel]]~~ first electrode; and
forming ~~[[an]]~~ a second electrode over the light emitting layer,
wherein a surface of the second electrode in contact with the light emitting layer is uneven.

49. (Currently amended) A method according to claim 48, further comprising:
forming ~~[[an]]~~ a second insulating film in a transverse direction of the layer, wherein the second insulating film has a ~~[[high]]~~ light absorption property.

50. (Currently amended) A method according to claim 48, further comprising:
forming a thin film transistor ~~[[an]]~~ over a substrate, wherein the thin film transistor comprises a semiconductor film and a gate electrode;
~~forming an insulating film over the thin film transistor;~~
forming a ~~[[first]]~~ second opening in the first insulating film; and
forming a wiring over the first insulating film, wherein the wiring is electrically connected to the semiconductor film through the ~~[[first]]~~ second opening; and
~~forming at least one second opening in the insulating film.~~

51. (Currently amended) A method according to claim 48, further comprising:
forming a thin film transistor ~~[[on]]~~ over a substrate, wherein the thin film transistor comprises a semiconductor film and a gate electrode;
~~forming an insulating film over the thin film transistor, wherein the insulating film has a high light absorption property;~~
forming a ~~[[first]]~~ second opening in the first insulating film; and
forming a wiring over the first insulating film, wherein the wiring is electrically connected to the semiconductor film through the ~~[[first]]~~ second opening; and
~~forming at least one second opening in the insulating film~~
wherein the first insulating film has a light absorption property.

52. (Currently amended) A method according to claim 48, further comprising:
forming a thin film transistor ~~[[on]]~~ over a substrate, wherein the thin film transistor comprises a semiconductor film and a gate electrode;
~~forming a first insulating film over the thin film transistor;~~
forming a ~~[[first]]~~ second opening in the first insulating film;
forming a wiring over the first insulating film, wherein the wiring is electrically connected to the semiconductor film through the ~~[[first]]~~ second opening;
forming a second insulating film in contact with the first insulating film; and
forming a ~~second~~ third opening in the second insulating film.

53. (Currently amended) A method according to claim 48, further comprising:
forming a thin film transistor ~~[[on]]~~ over a substrate, wherein the thin film transistor comprises a semiconductor film and a gate electrode;
~~forming a first insulating film over the thin film transistor;~~
forming a ~~[[first]]~~ second opening in the first insulating film;
forming a wiring over the first insulating film, wherein the wiring is electrically connected to the semiconductor film through the ~~[[first]]~~ second opening;

forming a second insulating film in contact with the first insulating film, wherein the second insulating film has a ~~[[high]]~~ light absorption property; and
forming a ~~second~~ third opening in the second insulating film.

54. (Currently amended) A method according to claim 48, wherein the light emitting layer comprises ~~at least one of~~ an organic material ~~and an inorganic material~~.

55. (Previously Presented) A method according to claim 48, wherein the layer has a protrusion.

56. (Canceled)

57. (Currently amended) A method according to claim 6, wherein the second electrode is a cathode.

58-59. (Canceled)

60. (Currently amended) A method according to claim 24, wherein the second electrode is a cathode.

61. (Currently amended) A method according to claim 32, wherein the second electrode is a cathode.

62. (Currently amended) A method according to claim 40, wherein the second electrode is a cathode.

63. (Currently amended) A method according to claim 48, wherein the second electrode is a cathode.